**Product data sheet** 

## 1. General description

The HEF4011B is a quad 2-input NAND gate. The outputs are fully buffered for the highest noise immunity and pattern insensitivity to output impedance.

It operates over a recommended  $V_{DD}$  power supply range of 3 V to 15 V referenced to  $V_{SS}$  (usually ground). Unused inputs must be connected to  $V_{DD}$ ,  $V_{SS}$ , or another input.

### 2. Features and benefits

- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Standardized symmetrical output characteristics
- Specified from –40 °C to +125 °C
- Complies with JEDEC standard JESD 13-B
- Inputs and outputs are protected against electrostatic effects

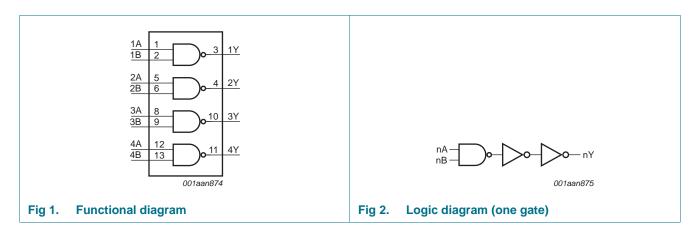
## 3. Ordering information

### Table 1.Ordering information

All types operate from -40 °C to +125 °C

Type number	Package	Package			
	Name	Description	Version		
HEF4011BP	DIP14	plastic dual in-line package; 14 leads (300 mil)	SOT27-1		
HEF4011BT	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1		

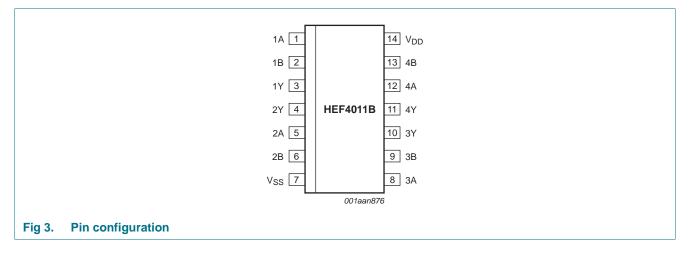
## 4. Functional diagram





## 5. Pinning information

### 5.1 Pinning



## 5.2 Pin description

Table 2.	Pin description	
Symbol	Pin	Description
nA	1, 5, 8, 12	input
nB	2, 6, 9, 13	input
nY	3, 4, 10, 11	output
V <sub>SS</sub> V <sub>DD</sub>	7	ground (0 V)
V <sub>DD</sub>	14	supply voltage

## 6. Functional description

### Table 3.Function table

Input		Output
nA	nB	nY
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

[1] H = HIGH voltage level; L = LOW voltage level.

## 7. Limiting values

### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to V<sub>SS</sub> = 0 V (ground).

					-
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DD</sub>	supply voltage		-0.5	+18	V
l <sub>IK</sub>	input clamping current	$V_{\rm I} < -0.5$ V or $V_{\rm I}$ > $V_{\rm DD}$ + 0.5 V	-	±10	mA
VI	input voltage		-0.5	$V_{DD} + 0.5$	V
I <sub>OK</sub>	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm DD}$ + 0.5 V	-	±10	mA
I <sub>I/O</sub>	input/output current		-	±10	mA
I <sub>DD</sub>	supply current		-	50	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>amb</sub>	ambient temperature		-40	+125	°C
P <sub>tot</sub>	total power dissipation	$T_{amb}$ = -40 °C to + 125 °C			
		DIP14	<u>[1]</u> _	750	mW
		SO14	[2] _	500	mW
Р	power dissipation	per output	-	100	mW

[1] For DIP14 packages: above  $T_{amb}$  = 70 °C,  $P_{tot}$  derates linearly with 12 mW/K.

[2] For SO14 packages: above  $T_{amb}$  = 70 °C, P<sub>tot</sub> derates linearly with 8 mW/K.

### 8. Recommended operating conditions

### Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DD</sub>	supply voltage		3	-	15	V
VI	input voltage		0	-	$V_{DD}$	V
T <sub>amb</sub>	ambient temperature	in free air	-40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{DD} = 5 V$	-	-	3.75	μs/V
		V <sub>DD</sub> = 10 V	-	-	0.5	μs/V
		V <sub>DD</sub> = 15 V	-	-	0.08	μs/V

Quad 2-input NAND gate

## 9. Static characteristics

### Table 6. Static characteristics

 $V_{SS} = 0$  V;  $V_l = V_{SS}$  or  $V_{DD}$ ; unless otherwise specified.

Symbol	Parameter	Conditions	V <sub>DD</sub>	T <sub>amb</sub> =	<b>−40</b> °C	T <sub>amb</sub> =	$T_{amb} = -40 \ ^{\circ}C \ T_{amb} = +25 \ ^{\circ}C \ ^{\circ}$		T <sub>amb</sub> = +85 °C		T <sub>amb</sub> = +125 °C	Unit	
				Min	Max	Min	Мах	Min	Max	Min	Max		
VIH	HIGH-level	$ I_0  < 1 \ \mu A$	5 V	3.5	-	3.5	-	3.5	-	3.5	-	V	
	input voltage		10 V	7.0	-	7.0	-	7.0	-	7.0	-	V	
			15 V	11.0	-	11.0	-	11.0	-	11.0	-	V	
V <sub>IL</sub>	LOW-level	$ I_0  < 1 \ \mu A$	5 V	-	1.5	-	1.5	-	1.5	-	1.5	V	
	input voltage		10 V	-	3.0	-	3.0	-	3.0	-	3.0	V	
			15 V	-	4.0	-	4.0	-	4.0	-	4.0	V	
V <sub>OH</sub>	HIGH-level	$ I_0  < 1 \ \mu A$	5 V	4.95	-	4.95	-	4.95	-	4.95	-	V	
	output voltage		10 V	9.95	-	9.95	-	9.95	-	9.95	-	V	
			15 V	14.95	-	14.95	-	14.95	-	14.95	-	V	
V <sub>OL</sub>			$ I_0  < 1 \ \mu A$	5 V	-	0.05	-	0.05	-	0.05	-	0.05	V
	output voltage		10 V	-	0.05	-	0.05	-	0.05	-	0.05	V	
			15 V	-	0.05	-	0.05	-	0.05	-	0.05	V	
I <sub>OH</sub>	HIGH-level	$V_{O} = 2.5 V$	5 V	-	-1.7	-	-1.4	-	-1.1	-	-1.1	mA	
	output current	V <sub>O</sub> = 4.6 V	5 V	-	-0.64	-	-0.5	-	-0.36	-	-0.36	mΑ	
		$V_{O} = 9.5 V$	10 V	-	-1.6	-	-1.3	-	-0.9	-	-0.9	mA	
		V <sub>O</sub> = 13.5 V	15 V	-	-4.2	-	-3.4	-	-2.4	-	-2.4	mA	
l <sub>OL</sub>	LOW-level	$V_O = 0.4 V$	5 V	0.64	-	0.5	-	0.36	-	0.36	-	mA	
	output current	$V_O = 0.5 V$	10 V	1.6	-	1.3	-	0.9	-	0.9	-	mA	
		V <sub>O</sub> = 1.5 V	15 V	4.2	-	3.4	-	2.4	-	2.4	-	mA	
I	input leakage current		15 V	-	±0.1	-	±0.1	-	±1.0	-	±1.0	μA	
I <sub>DD</sub>	supply current	all valid input	5 V	-	0.25	-	0.25	-	7.5	-	7.5	μΑ	
		combinations;	10 V	-	0.5	-	0.5	-	15.0	-	15.0	μΑ	
		I <sub>O</sub> = 0 A	15 V	-	1.0	-	1.0	-	30.0	-	30.0	μΑ	
Cı	input capacitance			-	-	-	7.5	-	-	-	-	pF	

## **10.** Dynamic characteristics

### Table 7. Dynamic characteristics

 $T_{amb} = 25$  °C; for waveforms see <u>Figure 4</u>; for test circuit see <u>Figure 5</u>; unless otherwise specified.

Symbol	Parameter	Extrapolation formula <sup>[1]</sup>	V <sub>DD</sub>	Min	Тур	Max	Unit
t <sub>pd</sub>	propagation delay	28 + 0.55 × C <sub>L</sub>	5 V	[2] _	55	110	ns
-		$14 + 0.23 \times C_L$	10 V	-	25	45	ns
		$12 + 0.16 \times C_L$	15 V	-	20	35	ns
t <sub>THL</sub>	HIGH to LOW output transition time	$10 + 1.00 \times C_L$	5 V	-	60	120	ns
		$9 + 0.42 \times C_L$	10 V	-	30	60	ns
		$6 + 0.28 \times C_L$	15 V	-	20	40	ns
t <sub>TLH</sub>	LOW to HIGH output transition time	$10 + 1.00 \times C_L$	5 V	-	60	120	ns
		$9 + 0.42 \times C_L$	10 V	-	30	60	ns
		$6 + 0.28 \times C_L$	15 V	-	20	40	ns

[1] The typical value of the propagation delay and output transition time can be calculated with the extrapolation formula (C<sub>L</sub> in pF).

[2]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

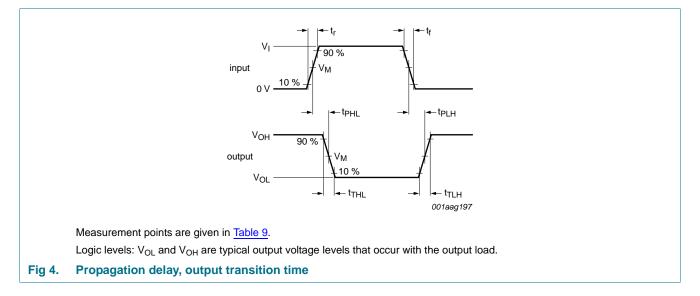
### Table 8. Dynamic power dissipation

 $V_{SS} = 0 V; t_r = t_f \le 20 ns; T_{amb} = 25 \ ^{\circ}C.$ 

Symbol	Parameter	$V_{\text{DD}}$	Typical formula	Where
PD	dynamic power dissipation	5 V	$P_D = 1300 \times f_i + \Sigma(f_o \times C_L) \times V_DD^2 \ (\muW)$	$f_i$ = input frequency in MHz;
		10 V	$P_D = 6000 \times f_i + \Sigma(f_o \times C_L) \times V_DD^2 \text{ (}\muW\text{)}$	$f_o = output frequency in MHz;$
		15 V	$P_{D} = 20100 \times f_{i} + \Sigma(f_{o} \times C_{L}) \times V_{DD}^2 \; (\muW)$	$C_L$ = output load capacitance in pF;
				$\Sigma(f_o \times C_L)$ = sum of the outputs;
				$V_{DD}$ = supply voltage in V.

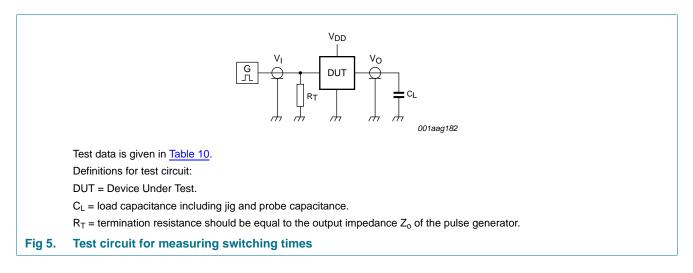
**Quad 2-input NAND gate** 

### 11. Waveforms



#### Table 9. **Measurement points**

Supply voltage	Input	Output
V <sub>DD</sub>	V <sub>M</sub>	V <sub>M</sub>
5 V to 15 V	0.5V <sub>DD</sub>	0.5V <sub>DD</sub>



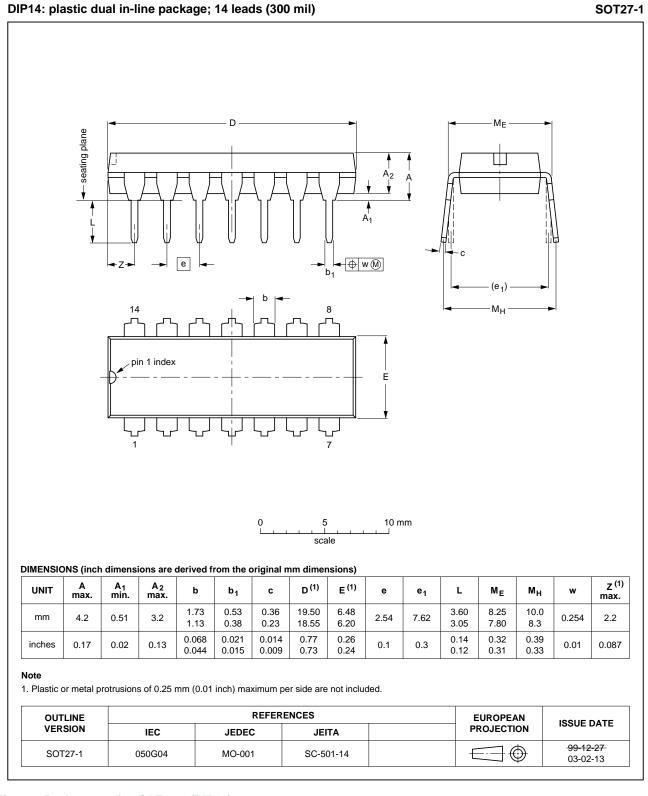
### Table 10. Test data

Supply voltage	Input		Load
V <sub>DD</sub>	VI	t <sub>r</sub> , t <sub>f</sub>	CL
5 V to 15 V	V <sub>SS</sub> or V <sub>DD</sub>	≤ 20 ns	50 pF

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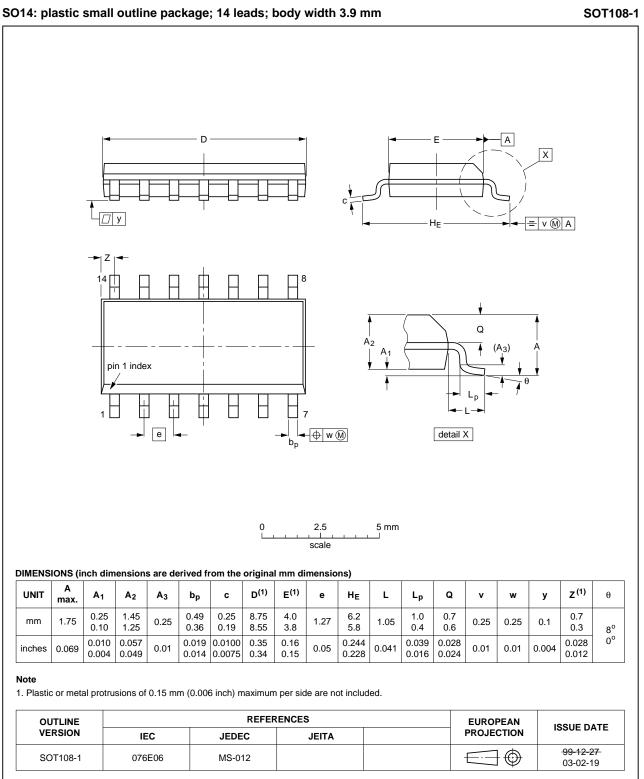
## 12. Package outline



### Fig 6. Package outline SOT27-1 (DIP14)

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#### Package outline SOT108-1 (SO14) Fig 7.

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## **13. Abbreviations**

Table 11.	1. Abbreviations	
Acronym	Description	
DUT	Device Under Test	

## 14. Revision history

Table 12. Revision hi	story					
Document ID	Release date	Data sheet status	Change notice	Supersedes		
HEF4011B v.5	20111121	Product data sheet	-	HEF4011B v.4		
Modifications:       • Legal pages updated.         • Changes in "General description" and "Features and benefits".         • Section "Applications" removed.						
HEF4011B v.4	20110330	Product data sheet	-	HEF4011B_CNV v.3		
HEF4011B_CNV v.3	19950101	Product specification	-	HEF4011B_CNV v.2		
HEF4011B_CNV v.2	19950101	Product specification	-	-		

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Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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